

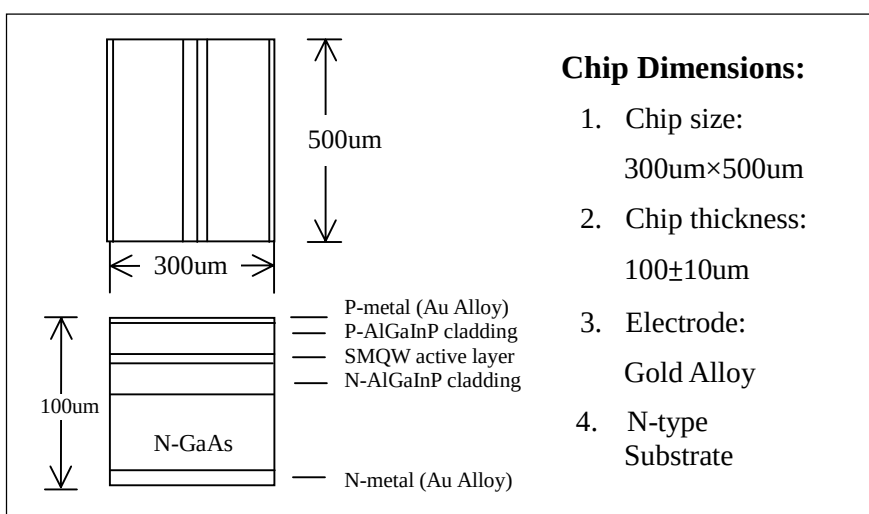
Preliminary

Essential:

- 780nm Laser Chip
- AlGaInP/GaAs
- MOVPE Process
- Strained MQW

Product Description:

UEL-H78 is a 780nm infrared high power LD chip fabricated from aluminum gallium indium phosphide (AlGaInP) MOVPE technology. The low threshold current is achieved by the use of strained multiple quantum well active layer structure. UEL-H78 LD chip is ideal for use as a light source for CD-R and other optical discs.



Great Performance:

- **Wavelength:** 785nm(typ.)
- **Output Power:** 40 mW CW
- **100% Probing**
- **Degradation Tests**
- **CD-R/MO/MD Applications**

Absolute Maximum Ratings (Tc=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Rated Optical Power	P_o	50	mW
Operating Temperature	T_{op}	-10~60	°C
Storage Temperature	T_{stg}	-20~85	°C
Reverse Voltage	V_{RLD}	2	V

Optical & Electrical Characteristics (Tc=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITION
Threshold Current	I_{th}	-	30	-	mA	CW
Operation Current	I_{op}	-	85	-	mA	$P_o=40mW$
Operation Voltage	V_{op}	-	1.9	-	V	$P_o=40mW$
Lasing Wavelength	λ_p	-	785	-	nm	$P_o=40mW$
Beam Divergence	$\Theta_{ }$	-	8		deg	$P_o=40mW$
	$\Theta_{\perp}$	-	38			FWHM

- I_{op} is measured on bare chips with UEC's tester.
- Bonding Condition Note: Die-bonding on a good heat sink.

Contact us:

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